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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	10/026,802
		Filing Date	December 27, 2001
		First Named Inventor	Hisashi Ohtani et al.
		Group Art Unit	2811
		Examiner Name	W. Mintel
Sheet 1 of 1	Attorney Docket Number	0756-2415	

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

FOREIGN PATENT DOCUMENTS								
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
zm		JP	63-318162		12/27/1988			Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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zm		Ultra LSI Process Data Handbook, April 15, 1982, pp. 124-125	Concise Stmt. MAY 12 2003

Examiner Signature	Date Considered	Jan 7, 2003
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<b>Form PTO-1449</b> (Rev. 8-83)	U.S. Department of Commerce Patent and Trademark Office	Docket No: 740756-2415	Serial No. Not Yet Assigned
<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)			
		Applicant: Hisashi OHTANI et al.	
		Filing Date: December 27, 2001	Group: 2811

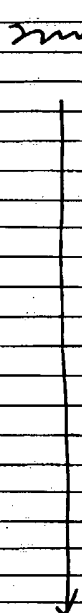

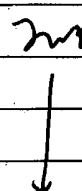
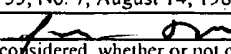
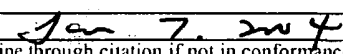
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\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<b>U.S. PATENT DOCUMENTS</b>						
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<b>U.S. PATENT DOCUMENTS</b>							
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Serial No. Not Yet  
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STATEMENT**

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Applicant: Hisashi OHTANI, et al.

Filing Date: December 27, 2001

Group: 2811

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